

**SEMICONDUCTOR MEMORY DEVICE WITH STANDBY CURRENT
FAILURE JUDGING FUNCTION AND METHOD FOR JUDGING
STANDBY CURRENT FAILURE**

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ABSTRACT OF THE DISCLOSURE

A semiconductor memory device which a pad for receiving a power voltage, a first power line connected to the pad, and a plurality of second power lines respectively connected to memory cells of a repair unit. A selection circuit outputs selection signals for selecting the memory cells of the array in the repair unit in response to a row address in a test operation mode. A power switch circuit operates in response to the selection signals, and connects the second power line connected to the selected memory cells with the first power line in the test operation mode. The power switch circuit disconnects the remaining second power lines from the first power line.

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